

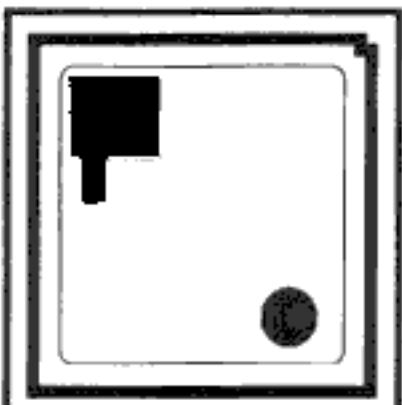

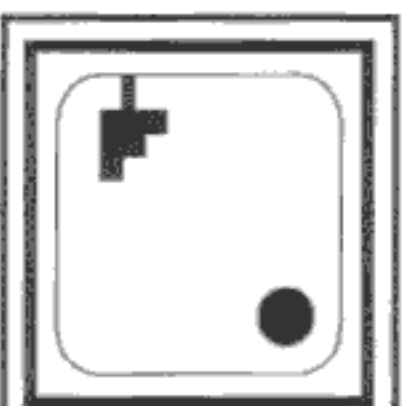
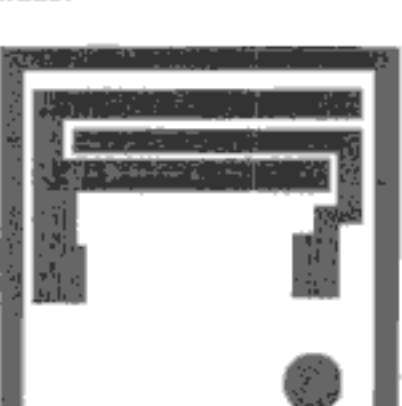


ABORN's opto chips are fabricated using the latest silicon technologies. These chips have exceptionally stable characteristics. Special screening is available. All chips are available in standard or custom packages.

Chip Topography	General Description	Typical Application	Typical Data Parameters	Chip Size (Mils)	Note
	FNX100 A large area silicon PIN photodiode chip with a large active area	<ul style="list-style-type: none"> · Fiber Optic Link · Digital Interfacing · Linear Interfacing 	<ul style="list-style-type: none"> · Photo active area 117X117 mils · BVR=30V · R=0.5A/W · C_J=35pF · tr, tr=100ns 	125X125	1
	FNX1010 A phototransistor chip with a wide range of sensitivities	<ul style="list-style-type: none"> · Optoisolators · Photo Sensors 	<ul style="list-style-type: none"> · V_{CEO}=50V · I_{CEO}=10nA · I_{CE(IT)}=4.5mA · tr, tr=10ms 	40X40	1
	FNX1016 A general purpose phototransistor chip with a wide range of sensitivities	<ul style="list-style-type: none"> · Optoisolators · Photo Sensors 	<ul style="list-style-type: none"> · V_{CEO}=50V · I_{CEO}=10nA · I_{CE(IT)}=1.5mA · tr, tr=3.0ms 	25X25	1
	FNX1051 A photodarlington chip with a range of high sensitivities	<ul style="list-style-type: none"> · Optoisolators · Photo Sensors 	<ul style="list-style-type: none"> · V_{CEO}=60V · I_{CEO}=10nA · I_{CE(IT)}=80mA · tr, tr=100ms 	42X34	1
	FNX1055 A phototransistor chip with a high breakdown voltage	<ul style="list-style-type: none"> · Optoisolators · Photo Sensors 	<ul style="list-style-type: none"> · V_{CEO}=300V · I_{CEO}=1nA · I_{CE(IT)}=0.6mA · tr, tr=5.0ms 	28X28	1
	FNX1056 A photodarlington chip with a range of high sensitivities	<ul style="list-style-type: none"> · Optoisolators · Photo Sensors 	<ul style="list-style-type: none"> · V_{CEO}=60V · I_{CEO}=10nA · I_{CE(IT)}=50mA · tr, tr=80ms 	22X34	1